



# Wireless Components

ASK Single Conversion Receiver TDA 5200 Version 2.7

Specification March 2000

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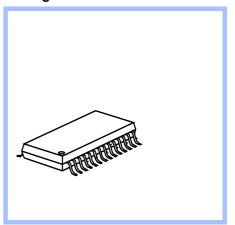
**Product Info** 

#### **Product Info**

#### **General Description**

The IC is a very low power consumption single chip ASK Single Conversion Receiver for the frequency bands 868-870 MHz and 433-435 MHz. The IC offers a high level of integration and needs only a few external components. The device contains a low noise amplifier (LNA), a double balanced mixer, a fully integrated VCO, a PLL synthesiser, a crystal oscillator, a limiter with RSSI generator, a data filter, a data comparator (slicer) and a peak detector. Additionally there is a power down feature to save battery life.

#### **Package**



#### **Features**

- Low supply current (I<sub>s</sub> = 4.8mA typ. at 868MHz, I<sub>s</sub> = 4.6mA typ. at 434MHz)
- Supply voltage range 5V ±10%
- Power down mode with very low supply current (50nA typ)
- Fully integrated VCO and PLL Synthesiser
- RF input sensitivity < -107dBm

- Selectable frequency ranges 868-870 MHz and 433-435 MHz
- Limiter with RSSI generation, operating at 10.7MHz
- Selectable reference frequency
- 2nd order low pass data filter with external capacitors
- Data slicer with self-adjusting threshold

#### **Application**

- Keyless Entry Systems
- Remote Control Systems
- Alarm Systems
- Low Bitrate Communication Systems

#### **Ordering Information**

Туре	Ordering Code	Package
TDA 5200	Q67037-A1049	P-TSSOP-28-1
available on tape and reel		

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# Product Description

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**Product Description** 



#### 2.1 Overview

The IC is a very low power consumption single chip ASK Single Conversion Receiver for the frequency bands 868-870 MHz and 433-435 MHz. The IC offers a high level of integration and needs only a few external components. The device contains a low noise amplifier (LNA), a double balanced mixer, a fully integrated VCO, a PLL synthesiser, a crystal oscillator, a limiter with RSSI generator, a data filter, a data comparator (slicer) and a peak detector. Additionally there is a power down feature to save battery life.

### 2.2 Application

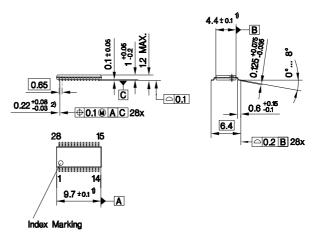
- Keyless Entry Systems
- Remote Control Systems
- Alarm Systems
- Low Bitrate Communication Systems

#### 2.3 Features

- Low supply current (I<sub>s</sub> = 4.8 mA typ. at 868MHz, 4.6mA typ. at 434MHz)
- Supply voltage range 5V ±10%
- Power down mode with very low supply current (100nA max.)
- Fully integrated VCO and PLL Synthesiser
- RF input sensitivity < -107dBm
- Selectable frequency ranges 868-870 MHz and 433-435 MHz
- Selectable reference frequency
- Limiter with RSSI generation, operating at 10.7MHz
- 2nd order low pass data filter with external capacitors
- Data slicer with self-adjusting threshold



## 2.4 Package Outlines



- 1) Does not include plastic or metal protrusion of 0.15 max. per side
- 2) Does not include dambar protrusion

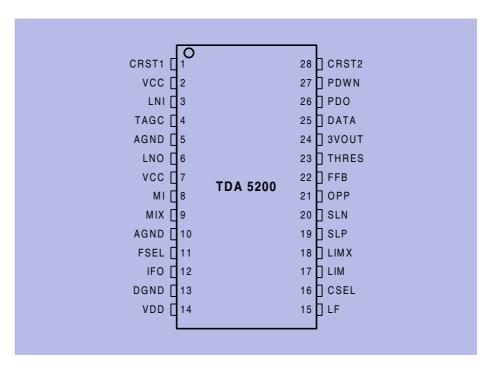
P\_TSSOP\_28.EPS

Figure 2-1 P-TSSOP-28-1 package outlines

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## 3.1 Pin Configuration



Pin\_Configuration.wmf

Figure 3-1 IC Pin Configuration



### 3.2 Pin Definition and Function

Table 3-	1 Pin Definition	n and Function	
Pin No.	Symbol	Equivalent I/O-Schematic	Function
1	CRST1	4.15V 50uA	External Crystal Connector 1
2	VCC		5V Supply
3	LNI	57uA 3 500uA	LNA Input



4	TAGC	4.3V 3uA 1.4uA	AGC Time Constant Control
5	AGND		Analogue Ground Return
6	LNO	5V	LNA Output
7	VCC		5V Supply
9	MIX	1.7V 2k 2k 400uA	Mixer Input  Complementary Mixer Input
10	AGND		Analogue Ground Return



11	FSEL		869/434 MHz Operating Frequency Selector
		1.2V • 750	
		11	
12	IFO		10.7 MHz IF Mixer Output
		300uA	
		2.2V	
		12	
		4.5k	
		$\perp$	
13	DGND		Digital Ground Return
14	VDD		5V Supply (PLL Counter Circuitry)
15	LF		PLL Filter Access Point
		5V 4.6V	
		<u>†</u>	
		15 100 30uA	
		30uA	
		2.4V	



16	CSEL	80k	6.xx or 13.xx MHz Quartz Selector
17	LIM		Limiter Input
17	LIIVI	2.4V 15k	
18	LIMX		Complementary Limiter Input
		330 75uA	
		∐ 15k T	
		ļ	
19	SLP	19 100 3k 40uA	Data Slicer Positive Input

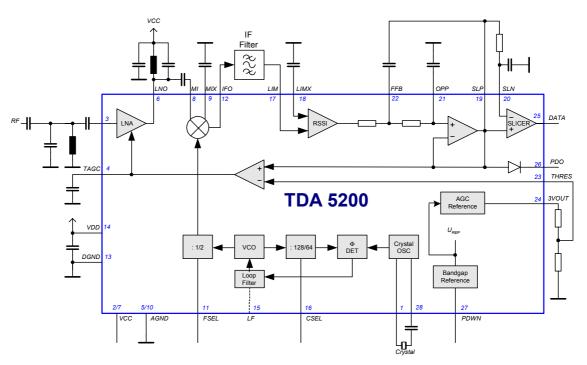


20	SLN	20 10k	Data Slicer Negative Input
21	OPP	21 200 5uA	OpAmp Noninverting Input
22	FFB	100k	Data Filter Feedback Pin
23	THRES	23 10k	AGC Threshold Input
24	3VOUT	24 <b>3</b> V	3V Reference Output



25	DATA	25 200 80k	Data Output
26	PDO	26	Peak Detector Output
27	PDWN	220k	Power Down Input
28	CRST2	4.15V 50uA	External Crystal Connector 2

## 3.3 Functional Block Diagram



Function\_5200.wmf

Figure 3-2 Main Block Diagram



#### 3.4 Functional Blocks

#### 3.4.1 Low Noise Amplifier (LNA)

The LNA is an on-chip cascode amplifier with a voltage gain of 15 to 20dB. The gain figure is determined by the external matching networks situated ahead of LNA and between the LNA output LNO (Pin 6) and the Mixer Inputs MI and MIX (Pins 8 and 9). The noise figure of the LNA is approximately 3.2dB, the current consumption is 500µA. The gain can be reduced by approximately 18dB. The switching point of this AGC action can be determined externally by applying a threshold voltage at the THRES pin (Pin 23). This voltage is compared internally with the received signal (RSSI) level generated by the limiter circuitry. In case that the RSSI level is higher than the threshold voltage the LNA gain is reduced and vice versa. The threshold voltage can be generated by attaching a voltage divider between the **3VOUT** pin (Pin 24) which provides a temperature stable 3V output generated from the internal bandgap voltage and the **THRES** pin as described in Section 4.1. The time constant of the AGC action can be determined by connecting a capacitor to the TAGC pin (Pin 4) and should be chosen along with the appropriate threshold voltage according to the intended operating case and interference scenario to be expected during operation. The optimum choice of AGC time constant and the threshold voltage is described in Section 4.1.

#### 3.4.2 Mixer

The Double Balanced Mixer downconverts the input frequency (RF) in the range of 433-435MHz/868-870MHz to the intermediate frequency (IF) at 10.7MHz with a voltage gain of approximately 21dB. A low pass filter with a corner frequency of 20MHz is built on chip in order to suppress RF signals to appear at the IF output ( **IFO** pin). The IF output is internally consisting of an emitter follower that has a source impedance of approximately 330  $\Omega$  to facilitate interfacing the pin directly to a standard 10.7MHz ceramic filter without additional matching circuitry.

#### 3.4.3 PLL Synthesizer

The Phase Locked Loop synthesiser consists of a VCO, an asynchronous divider chain, a phase detector with charge pump and a loop filter and is fully implemented on-chip. The VCO is including spiral inductors and varactor diodes. It's nominal centre frequency is 852MHz. No additional components are necessary. The oscillator signal is fed both to the synthesiser divider chain and to the downconverting mixer. In case of operation in the 433 - 435 MHz range, the signal is divided by two before it is fed to the mixer. This is controlled by the selection pin **FSEL** (Pin 11) as described in the following table. The overall divi-



sion ratio of the divider chain can be selected to be either 128 or 64, depending on the frequency of the reference oscillator quartz (see below). The loop filter is also realised fully on-chip.

Table 3-2 FSEL pin operating states	
FSEL	RF Frequency
Open	433 - 435 MHz
Shorted to ground	868 - 870 MHz

#### 3.4.4 Crystal Oscillator

The on-chip crystal oscillator circuitry allows for utilisation of quartzes both in the 6 and 13MHz range as the overall division ratio of the PLL can be switched between 64 and 128 via the **CSEL** (Pin 16) pin according to the following table.

Table 3-3 CSEL pin operating states	
CSEL	Crystal Frequency
Open	6.xx MHz
Shorted to ground	13.xx MHz

The calculation of the value of the necessary quartz load capacitance is shown in Section 4.3, the quartz frequency calculation is expained in Section 4.4.

#### 3.4.5 Limiter

The Limiter is an AC coupled multistage amplifier with a cumulative gain of approximately 80dB that has a bandpass-characteristic centred around 10.7MHz. It has an input impedance of 330  $\Omega$  to allow for easy interfacing to a 10.7MHz ceramic IF filter. The limiter circuit acts as a Receive Signal Strength Indicator (RSSI) generator which produces a DC voltage that is directly proportional to the input signal level as can be seen in Figure 4-2. This signal is used to demodulate the ASK receive signal in the subsequent baseband circuitry and to turn down the LNA gain by approximately 17dB in case the input signal strength is too strong as described in Section 3.4.1 and Section 4.1.

#### 3.4.6 Data Filter

The data filter comprises an OP-Amp with a bandwidth of 100kHz used as a voltage follower and two  $100k\Omega$  on-chip resistors. Along with two external capacitors a 2nd order Sallen-Key low pass filter is formed. The selection of the capacitor values is described in Section 4.2.



#### 3.4.7 Data Slicer

The data slicer is a fast comparator with a bandwidth of 100 kHz. This allows for a maximum receive data rate of approximately 120kBaud. The maximum achievable data rate also depends on the IF Filter bandwidth and the local oscillator tolerance values. Both inputs are accessible. The output delivers a digital data signal (CMOS-like levels) for the detector. The self-adjusting threshold on pin 20 its generated by RC-term or peak detector depending on the baseband coding scheme. The data slicer threshold generation alternatives are described in more detail in Section 4.5.

#### 3.4.8 Peak Detector

The peak detector generates a DC voltage which is proportional to the peak value of the receive data signal. An external RC network is necessary. The output can be used as an indicator for the signal strength and also as a reference for the data slicer. The maximum output current is  $500\mu$ A.

#### 3.4.9 Bandgap Reference Circuitry

A Bandgap Reference Circuit provides a temperature stable reference voltage for the device. A power down mode is available to switch off all subcircuits which is controlled by the PWDN pin (Pin 27) as shown in the following table. The supply current drawn in this case is typically 50nA.

Table 3-4 PDWN pin operating states	
PDWN	Operating State
Open or tied to ground	Powerdown Mode
Tied to Vs	Receiver On

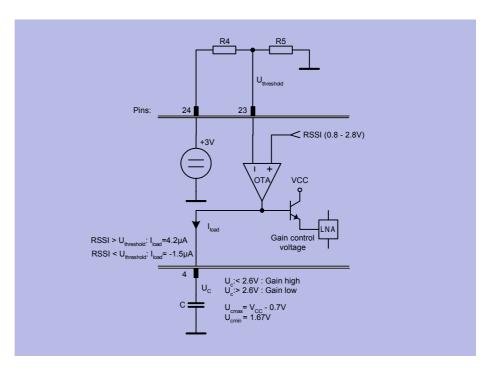
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#### 4.1 Choice of LNA Threshold Voltage and Time Constant

In the following figure the internal circuitry of the LNA automatic gain control is shown.



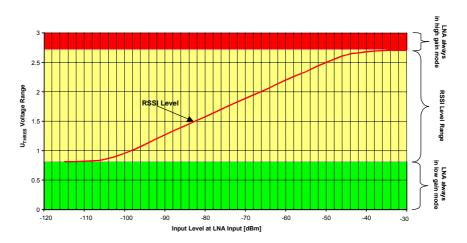
LNA\_autom.wmf

Figure 4-1 LNA Automatic Gain Control Circuitry

The LNA automatic gain control circuitry consists of an operational transimpedance amplifier that is used to compare the received signal strength signal (RSSI) generated by the Limiter with an externally provided threshold voltage  $U_{thres}$ . As shown in the following figure the threshold voltage can have any value between approximately 0.8 and 2.8V to provide a switching point within the receive signal dynamic range.

This voltage  $U_{thres}$  is applied to the **THRES** pin (Pin 23) The threshold voltage can be generated by attaching a voltage divider between the **3VOUT** pin (Pin 24) which provides a temperature stable 3V output generated from the internal bandgap voltage and the **THRES** pin. If the RSSI level generated by the Limiter is higher than  $U_{thres}$ , the OTA generates a positive current  $I_{load}$ . This yields a voltage rise on the **TAGC** pin (Pin 4). Otherwise, the OTA generates a negative current. These currents do not have the same values in order to achieve a fast-attack and slow-release action of the AGC and are used to charge an external capacitor which finally generates the LNA gain control voltage.





RSSI-AGC.wmf

Figure 4-2 RSSI Level and Permissive AGC Threshold Levels

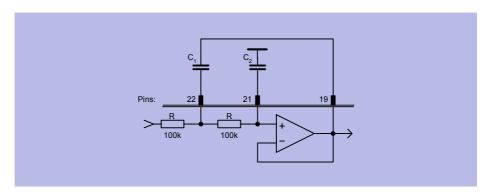
The switching point should be chosen according to the intended operating scenario. The determination of the optimum point is described in the accompanying Application Note, a threshold voltage level of 1.8V is apparently a viable choice. It should be noted that the output of the 3VOUT pin is capable of driving up to 50µA, but that the THRES pin input current is only in the region of 40nA. As the current drawn out of the 3VOUT pin is directly related to the receiver power consumption, the power divider resistors should have high impedance values. R4 can be chosen as  $120k\Omega$ , R5 as  $180k\Omega$  to yield an overall 3VOUT output current of  $10\mu$ A.

**Note:** If the LNA gain shall be kept in either high or low gain mode this has to be accomplished by tying the **THRES** pin to a fixed voltage. In order to achieve high gain mode operation, a voltage higher than 2.8V shall be applied to the **THRES** pin, such as a short to the **3VOLT** pin. In order to achieve low gain mode operation a voltage lower than 0.7V shall be applied to the **THRES**, such as a short to ground.

As stated above the capacitor connected to the **TAGC** pin is generating the gain control voltage of the LNA due to the charging and discharging currents of the OTA and thus is also responsible for the AGC time constant. As the charging and discharging currents are not equal two different time constants will result. The time constant corresponding to the charging process of the capacitor shall be chosen according to the data rate. According to measurements performed at Infineon the capacitor value should be greater than 47nF.

#### 4.2 Data Filter Design

Utilising the on-board voltage follower and the two  $100k\Omega$  on-chip resistors a 2nd order Sallen-Key low pass data filter can be constructed by adding 2 external capacitors between pins 19 (SLP) and 22 (FFB) and to pin 21 (OPP) as depicted in the following figure and described in the following formulas  $^1$ .



Filter Design.wmf

Figure 4-3 Data Filter Design

$$C1 = \frac{2Q\sqrt{b}}{R2\Pi f_{3dB}} \qquad C2 = \frac{\sqrt{b}}{4QR\Pi f_{3dB}}$$

with

$$Q = \frac{\sqrt{b}}{a}$$

(3) the quality factor of the poles

where

in case of a Bessel filter a = 1.3617, b = 0.618

and thus Q = 0.577

and in case of a Butterworth filter a = 1.141, b = 1

and thus Q = 0.71

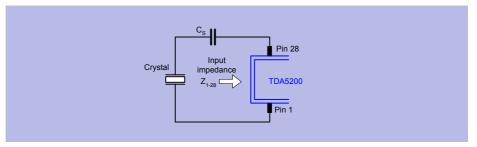
Example: Butterworth filter with  $f_{3dB} = 5kHz$  and  $R = 100k\Omega$ :

$$C_1 = 450pF, C_2 = 225pF$$

1. taken from Tietze/Schenk: Halbleiterschaltungstechnik, Springer Berlin, 1999

#### 4.3 Quartz Load Capacitance Calculation

The value of the capacitor necessary to achieve that the quartz oscillator is operating at the intended frequency is determined by the reactive part of the negative resistance of the oscillator circuit as shown in Section 5.1.3 and by the quartz specifications given by the quartz manufacturer.



Quartz load wmf

Figure 4-4 Determination of Series Capacitance Value for the Quartz Oscillator

Crystal specified with load capacitance

$$C_S = \frac{1}{\frac{1}{C_I} + 2\pi f X_L}$$

with C<sub>I</sub> the load capacitance (refer to the quartz crystal specification).

#### Examples:

These values may be obtained in high accuracy by putting two capacitors in series to the quartz, such as 20pF and 15pF in the 6.7MHz case and 15pF and 8.2pF in the 13.401MHz case.

#### 4.4 Quartz Frequency Calculation

The quartz frequency is calculated by using the following formula:

$$f_{\text{QU}} = (f_{\text{RF}} \pm 10.7) / r$$
 (1),

with  $f_{\rm RF}$  .... receive frequency

 $f_{LO}$  .... local oscillator (PLL) frequency ( $f_{RF} \pm 10.7$ )

 $f_{\rm QU}$  .... quartz oscillator frequency

r .... ratio of local oscillator (PLL) frequency and quartz

frequency as shown in the subsequent table.

Table 4-1 PLL Division Ratio Dependence on States of FSEL and CSEL								
FSEL	CSEL	Ratio $r = (f_{LO}/f_{QU})$						
open	open	64						
open	GND	32						
GND	open	128						
GND	GND	64						

Subtraction of 10.7 occurs in case the receive frequency is higher than the intended local oscillator frequency, addition in case the receive frequency lies below the local oscillator frequency.

Examples:

$$f_{\text{QU}} = (868.4MHz - 10.7MHz)/64 = 13.40156MHz$$

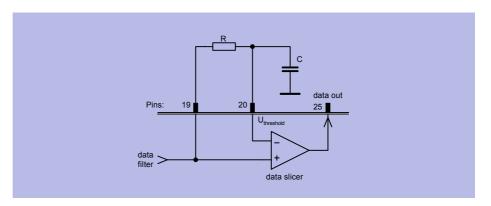
$$f_{\rm QU} = \left(868.4MHz - 10.7MHz\right)/128 = 6.7008\,MHz$$

$$f_{\text{QU}} = (434.2 \, MHz - 10.7 \, MHz) / 32 = 13.23437 \, MHz$$



#### 4.5 Data Slicer Threshold Generation

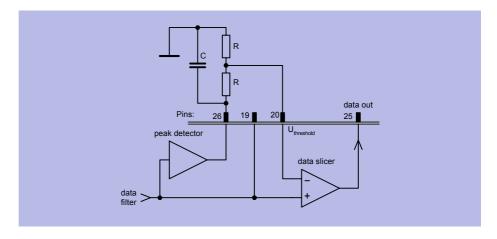
The threshold of the data slicer can be generated in two ways, depending on the signal coding scheme used. In case of a signal coding scheme without DC content such as Manchester coding the threshold can be generated using an external R-C integrator as shown in the following . The cut-off frequency of the R-C integrator has to be lower than the lowest frequency appearing in the data signal. In order to keep distortion low, the minimum value for R is  $20k\Omega$ .



Data slice1.wmf

Figure 4-5 Data Slicer Threshold Generation with External R-C Integrator

Another possibility for threshold generation is to use the peak detector in connection with two resistors and one capacitor as shown in the following figure. The component values are depending on the coding scheme and the protocol used.



Data\_slice2.wm

Figure 4-6 Data Slicer Threshold Generation Utilising the Peak Detector

# 5.1 Electrical Data. 5-2 5.2 Test Circuit 5-9 5.3 Test Board Layouts 5-10 5.4 Bill of Materials 5-12

#### 5.1 Electrical Data

#### 5.1.1 Absolute Maximum Ratings



#### **WARNING**

The maximum ratings may not be exceeded under any circumstances, not even momentarily and individually, as permanent damage to the IC will result.

Tabl	e 5-1 Absolute Maximum Ratings, Ambient te	emperature T <sub>AM</sub>	<sub>B</sub> =-40°C .	+ 85°C		
#	Parameter	Symbol	Limit '	Values	Unit	Remarks
			min	max		
1	Supply Voltage	$V_s$	-0.3	5.5	V	
2	Junction Temperature	Тj	-40	+150	°C	
3	Storage Temperature	T <sub>s</sub>	-40	+125	°C	
4	Thermal Resistance	R <sub>thJA</sub>		114	K/W	
5	ESD integrity, all pins	V <sub>ESD</sub>	-1	+1	kV	HBM according to MIL STD 883D, method 3015.7

#### 5.1.2 Operating Range

Within the operating range the IC operates as explained in the circuit description. The AC/DC characteristic limits are not guaranteed.

Supply voltage: VCC = 4.5V .. 5.5V

Та	Table 5-2 Operating Range, Ambient temperature T <sub>AMB</sub> = -40°C + 85°C							
#	Parameter	Symbol	Limit \	/alues	Unit	Test Conditions	L	Item
			min	max				
1	Supply Current	I <sub>S 868</sub>		5.6	mA	f <sub>RF</sub> = 868MHz		
		I <sub>S 434</sub>		5.4	mA	$f_{RF} = 434MHz$		
2	Receiver Input Level	RF <sub>in</sub>	-107	-13	dBm	@ source impedance $50Ω$ , BER 2E-3, average power level, Manchester encoded datarate 4kBit, 280kHz IF Bandwidth	•	
3	LNI Input Frequency	f <sub>RF</sub>	433/ 868	435/ 870	MHz			
4	MI/X Input Frequency	f <sub>MI</sub>	433/ 868	435/ 870	MHz			
5	3dB IF Frequency Range	f <sub>IF -3dB</sub>	5	23	MHz			
6	Powerdown Mode On	PWDN <sub>ON</sub>	0	0.8	٧			
7	Powerdown Mode Off	PWDN <sub>OFF</sub>	2	٧ <sub>S</sub>	٧			
8	Gain Control Voltage, LNA high gain state	V <sub>THRES</sub>	2.8	V <sub>S</sub>	V			
9	Gain Control Voltage, LNA low gain state	V <sub>THRES</sub>	0	0.7V	V			

<sup>■</sup> This value is guaranteed by design.

#### 5.1.3 AC/DC Characteristics

AC/DC characteristics involve the spread of values guaranteed within the specified voltage and ambient temperature range. Typical characteristics are the median of the production. The device performance parameters marked with ■ were measured on an Infineon evaluation board as desdribed in Section 5.2..

Та	Table 5-3 AC/DC Characteristics with T <sub>A</sub> 25 °C, V <sub>VCC</sub> = 4.5 5.5 V									
#	Parameter	Symbol		Limit Valu	ies	Unit	Test Conditions	L	Item	
			min	typ	max					
Su	Supply									
Su	pply Current									
1	Supply current, standby mode	I <sub>S PDWN</sub>		50	70	nA	Pin 27 (PDWN) open or tied to 0 V			
2	Supply current, device operating at 868MHz	I <sub>S 868</sub>		4.8	5.2	mA	Pin 11 (FSEL) tied to GND			
3	Supply current, device operating at 434 MHz	I <sub>S 434</sub>		4.6	5	mA	Pin 11 (FSEL) open			
LN	LNA									
Sig	gnal Input LNI (PIN 3),  V <sub>THF</sub>	<sub>RES</sub> > 2.8V, h	igh gair	n mode						
1	Average Power Level at BER = 2E-3 (Sensitivity)	RF <sub>in</sub>		-110		dBm	Manchester encoded datarate 4kBit, 280kHz IF Bandwidth	•		
2	Input impedance, f <sub>RF</sub> =434 MHz	S <sub>11 LNA</sub>	0.	873 / -34.7	' deg			•		
3	Input impedance, f <sub>RF</sub> =869 MHz	S <sub>11 LNA</sub>	0.	738 / -73.5	deg			•		
4	Input level @ 1dB compression	P1dB <sub>LNA</sub>		-15		dBm				
5	Input 3 <sup>rd</sup> order intercept point f <sub>RF</sub> =434 MHz	IIP3 <sub>LNA</sub>		-10		dBm	matched input	•		
6	Input 3 <sup>rd</sup> order intercept point f <sub>RF</sub> =869 MHz	IIP3 <sub>LNA</sub>		-14		dBm	matched input	•		
7	LO signal feedthrough at antenna port	LO <sub>LNI</sub>			-73	dBm		•		
Siç	gnal Output LNO (PIN 6), V <sub>T</sub>	HRES > 2.8V	, high g	ain mode						
1	Gain f <sub>RF</sub> =434 MHz	S <sub>21 LNA</sub>	1.5	509 / 138.2	2 deg					
2	Gain f <sub>RF</sub> =869 MHz	S <sub>21 LNA</sub>	1.4	419 / 101.7	7 deg					
3	Output impedance, f <sub>RF</sub> =434 MHz	S <sub>22 LNA</sub>	0.	886 / -12.9	deg			•		



Та	ble 5-3 AC/DC Characteris	tics with T <sub>A</sub>	25 °C, V	vcc = 4.5	5.5 V (c	ontinue	d)		
	Parameter	Symbol	l	Limit Valu	es	Unit	Test Conditions	L	Item
			min	typ	max				
4	Output impedance, f <sub>RF</sub> =869 MHz	S <sub>22 LNA</sub>	0.8	866 / -24.2	deg!			•	
5	Voltage Gain Antenna to MI f <sub>RF</sub> =434 MHz	G <sub>AntMI</sub>		42		dB			
6	Voltage Gain Antenna to MI f <sub>RF</sub> =869 MHz	G <sub>AntMI</sub>		40		dB			
7	Noise Figure	NF <sub>LNA</sub>		t.b.d.		dB			
Siç	gnal Input LNI, V <sub>THRES</sub> = GN	ND, low gain	mode						
1	Input impedance, f <sub>RF</sub> =434 MHz	S <sub>11 LNA</sub>	0.8	873 / -34.7	' deg			•	
2	Input impedance, f <sub>RF</sub> =869 MHz	S <sub>11 LNA</sub>	0.	738 / -73.5	deg			•	
3	Input level @ 1dB C. P f <sub>RF</sub> = 434 MHz	P1dB <sub>LNA</sub>		-18		dBm	matched input	•	
4	Input level @ 1dB C. P f <sub>RF</sub> = 869 MHz	P1dB <sub>LNA</sub>		-6		dBm	matched input	•	
5	Input 3 <sup>rd</sup> order intercept point f <sub>RF</sub> =434 MHz	IIP3 <sub>LNA</sub>		-10		dBm	matched input	ľ	
6	Input 3 <sup>rd</sup> order intercept point f <sub>RF</sub> =869 MHz	IIP3 <sub>LNA</sub>		-5		dBm	matched input	•	
Siç	gnal Output LNO, V <sub>THRES</sub> =	GND, low ga	ain mod	е					
1	Gain f <sub>RF</sub> =434 MHz	S <sub>21 LNA</sub>	0.1	183 / 140.6	6 deg				
2	Gain f <sub>RF</sub> =869 MHz	S <sub>21 LNA</sub>	0.	179 / 109.	1deg				
3	Output impedance, f <sub>RF</sub> =434 MHz	S <sub>22 LNA</sub>	0.8	897 / -13.6	deg			•	
4	Output impedance, f <sub>RF</sub> =869 MHz	S <sub>22 LNA</sub>	0.8	868 / -26.3	deg			•	
5	Voltage Gain Antenna to MI f <sub>RF</sub> =434 MHz	G <sub>AntMI</sub>		22		dB			
6	Voltage Gain Antenna to MI f <sub>RF</sub> =869 MHz	G <sub>AntMI</sub>		19		dB			
7	Noise Figure	NF <sub>LNA</sub>		t.b.d.		dB		•	
Siç	gnal 3VOUT (PIN 24)								
1	Output voltage	V <sub>3VOUT</sub>		3		V			
2	Current out	I <sub>3VOUT</sub>			50	μΑ			
Siç	gnal THRES (PIN 23)								
1	Input Voltage range	V <sub>THRES</sub>	0		V <sub>S</sub> -1V	V	see Section 4.1		



Та	ble 5-3 AC/DC Characterist	tics with T <sub>A</sub>	25 °C, V	vcc = 4.5	5.5 V (c	ontinue	d)			
	Parameter	Symbol		Limit Valu	es	Unit	Test Conditions	L	Item	
			min	typ	max					
2	LNA low gain mode	V <sub>THRES</sub>	0			V				
3	LNA high gain mode	V <sub>THRES</sub>	2.8	3	V <sub>S</sub>	V	or shorted to Pin 24			
4	Current in	I <sub>THRES_in</sub>		5		nA				
Siç	Signal TAGC (PIN 4)									
1	Current out, LNA low gain state	I <sub>TAGC_out</sub>		4.2		μA	RSSI > V <sub>THRES</sub>			
2	Current in, LNA high gain state	I <sub>TAGC_in</sub>		1.5		μA	RSSI < V <sub>THRES</sub>			
MI	XER									
Sig	gnal Input MI/MIX (PINS 8/9)									
1	Input impedance, f <sub>RF</sub> =434 MHz	S <sub>11 MIX</sub>	0.	942 / -14.4	deg			•		
2	Input impedance, f <sub>RF</sub> =869 MHz	S <sub>11 MIX</sub>	0.	918 / -28.1	deg			•		
3	Input 3 <sup>rd</sup> order intercept point f <sub>RF</sub> =434 MHz	IIP3 <sub>MIX</sub>		-28		dBm				
4	Input 3 <sup>rd</sup> order intercept point f <sub>RF</sub> =869 MHz	IIP3 <sub>MIX</sub>		-26		dBm		•		
Siç	gnal Output IFO (PIN 12)									
1	Output impedance	Z <sub>IFO</sub>		330		Ω				
2	Conversion Voltage Gain f <sub>RF</sub> =434 MHz	G <sub>MIX</sub>		+19		dB				
3	Conversion Voltage Gain f <sub>RF</sub> =869 MHz	G <sub>MIX</sub>		+18		dB				
4	Noise Figure, SSB (~DSB NF+3dB)	NF <sub>MIX</sub>		t.b.d.		dB		•		
5	RF to IF isolation	A <sub>RF-IF</sub>		t.b.d.		dB				
LII	MITER									
Sig	gnal Input LIM/X (PINS 17/18	3)								
1	Input Impedance	$Z_{LIM}$	264	330	396	Ω				
2	RSSI dynamic range	DR <sub>RSSI</sub>	60		80	dB				
3	RSSI linearity	LIN <sub>RSSI</sub>		±1		dB				
4	Operating frequency (3dB points)	f <sub>LIM</sub>	5	10.7	23	MHz		•		



	Parameter	Symbol		Limit Valu	es	Unit	Test Conditions	L	Item
			min	typ	max				
D <i>A</i>	DATA FILTER								
1	Useable bandwidth	BW <sub>BB</sub> FILT			100	kHz		•	
2	RSSI Level at Data Filter Output SLP	RSSI <sub>low</sub>	0.9			٧	LNA in high gain RF <sub>IN</sub> =-103dBm		
3	RSSI Level at Data Filter Output SLP	RSSI <sub>high</sub>			2.8	V	LNA in high gain. RF <sub>IN</sub> =-30dBm		
SL	ICER								
Sig	gnal Output DATA (PIN 25)								
1	Useable bandwith	BW <sub>BB</sub> SLIC			100	kHz		•	
2	Capacitive loading of output	C <sub>max</sub> SLIC			20	pF			
3	LOW output voltage	V <sub>SLIC_L</sub>		0		V			
4	HIGH output voltage	V <sub>SLIC_H</sub>			V <sub>S</sub> -1V	V			
5	Output current	I <sub>SLIC_out</sub>			200	μΑ			
PE	EAK DETECTOR								
Siç	gnal Output PDO (PIN 26)								
1	LOW output voltage	V <sub>SLIC_L</sub>		0		V			
2	HIGH output voltage	V <sub>SLIC_H</sub>			V <sub>S</sub> -1	V			
3	Load current	I <sub>load</sub>			500	μΑ			
4	Leakage current	I <sub>leakage</sub>		700		nA			
CF	RYSTAL OSCILLATOR								
	gnals CRSTL1, CRISTL 2, (F	PINS 1/28)							
1	Operating frequency	fCRSTL	6		14	MHz	fundamental mode, series resonance		
2	Input Impedance @ ~6MHz	Z <sub>1-28</sub>		-900 +j750		Ω		•	
3	Input Impedance @ ~13MHz	Z <sub>1-28</sub>		-450 +j1250		Ω		•	
4	Serial Capacity @ ~6MHz	C <sub>S 6</sub> =C1		8.7		pF			
5	Serial Capacity @ ~13MHz	C <sub>S13</sub> =C1		5.3		pF			

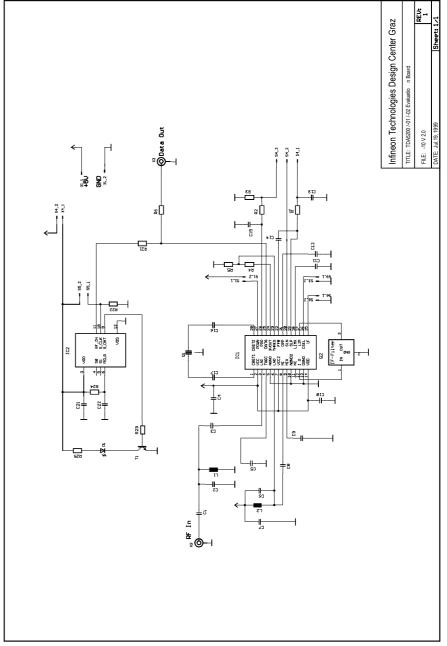


Та	ble 5-3 AC/DC Characteris	tics with T <sub>A</sub>	25 °C, V	vcc = 4.5	5.5 V (c	ontinue	d)		
	Parameter	Symbol		Limit Valu	ies	Unit	Test Conditions	L	Item
			min	typ	max				
PL	L								
Sig	gnal LF (PIN 15)			_					
1	Tuning voltage relative to V <sub>S</sub>	V <sub>TUNE</sub>	0.4	1.6	2.4	V			
PC	POWER DOWN MODE								
Sig	gnal PDWN (PIN 27)								
1	Powerdown Mode On	PWDN <sub>O</sub> N	0		0.8	V			
2	Powerdown Mode Off	PWDN <sub>Off</sub>	2.8		V <sub>S</sub>	V			
3	Input bias current PDWN	I <sub>PDWN</sub>		t.b.d.		μΑ			
4	Start-up Time until valid IF signal is detected	T <sub>SU</sub>			1	ms			
VC	O MULTIPLEXER								
Sig	gnal FSEL (PIN 11)								
1	f <sub>RF</sub> range 434 MHz	$V_{FSEL}$	1.4		4	V	or open		
2	f <sub>RF</sub> range 869 MHz	$V_{FSEL}$	0		0.2	V			
3	Input bias current FSEL	I <sub>FSEL</sub>		200		μΑ	FSEL tied to GND		
PL	L DIVIDER								
Siç	gnal CSEL (PIN 16)								
1	f <sub>CRSTL</sub> range 6.xxMHz	V <sub>CSEL</sub>	1.4		4	V	or open		
2	f <sub>CRSTL</sub> range 13.xxMHz	V <sub>CSEL</sub>	0		0.2	V			
3	Input bias current CSEL	ICSEL		5		μΑ	CSEL tied to GND		

<sup>■</sup> Measured only in lab.

#### 5.2 Test Circuit

The device performance parameters marked with in Section 5.1.3 were measured on an Infineon evaluation board. This evaluation board can be obtained together with evaluation boards of the accompanying transmitter device TDA5100 in an evaluation kit that may be ordered on the INFINEON RKE Webpage www.infineon.com/rke



Test\_circuit.wmf

Figure 5-1 Schematic of the Evaluation Board



## 5.3 Test Board Layouts

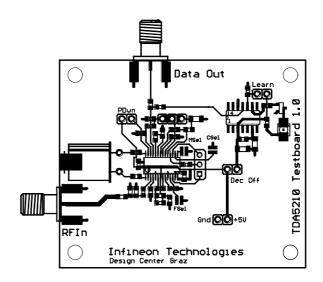


Figure 5-2 Top Side of the Evaluation Board

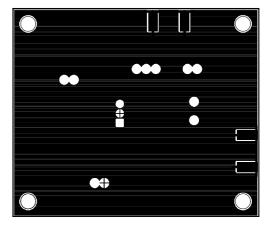


Figure 5-3 Bottom Side of the Evaluation Board

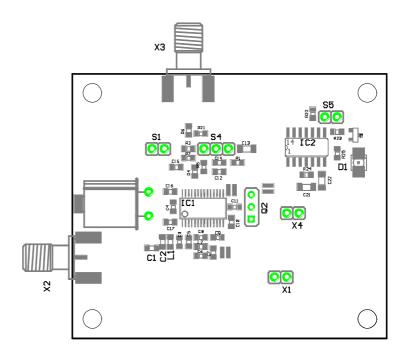


Figure 5-4 Component Placement on the Evaluation Board



#### 5.4 Bill of Materials

The following components are necessary for evaluation of the TDA5200 without use of a Microchip HCS515 decoder.

Table 5-4 Bill o	of Materials	
Ref	Value	Specification
R1	100kΩ	0805, ± 5%
R2	100kΩ	0805, ± 5%
R3	820kΩ	0805, ± 5%
R4	120kΩ	0805, ± 5%
R5	180kΩ	0805, ± 5%
R6	10kΩ	0805, ± 5%
L1	434 MHz: 15nH 869 MHz: 3.3nH	Toko, PTL2012-F15N0G Toko, PTL2012-F3N3C
L2	434 MHz: 8.2pF 869 MHz: 3.9nH	0805, COG, ± 0.1pF Toko, PTL2012-F3N9C
C1	1pF	0805, COG, ± 0.1pF
C2	434 MHz: 4.7pF 869 MHz: 3.9pF	0805, COG, ± 0.1pF 0805, COG, ± 0.1pF
C3	434 MHz: 6.8pF 869 MHz: 5.6pF	0805, COG, ± 0.1pF 0805, COG, ± 0.1pF
C4	100pF	0805, COG, ± 5%
C5	47nF	1206, X7R, ± 10%
C6	434 MHz: 10nH 869 MHz: 3.9pF	Toko, PTL2012-F10N0G 0805, COG, ± 0.1pF
C7	100pF	0805, COG, ± 5%
C8	434 MHz: 33pF 869 MHz: 22pF	0805, COG, ± 5% 0805, COG, ± 5%
C9	100pF	0805, COG, ± 5%
C10	10nF	0805, X7R, ± 10%
C11	10nF	0805, X7R, ± 10%
C12	220pF	0805, COG, ± 5%
C13	47nF	0805, X7R, ± 10%
C14	470pF	0805, COG, ± 5%
C15	47nF	0805, X7R, ± 5%
C16	15pF	0805, COG, ± 1%
C17	8.2pF	0805, COG, ± 1%
Q2	(f <sub>RF</sub> – 10.7MHz)/32 or (f <sub>RF</sub> – 10.7MHz)/64	HC49/U, fundamental mode, CL = 12pF, e.g. 434.2MHz: Jauch Q 13,23437-S11-1323-12-10/20 e.g. 868.4MHz: Jauch Q 13,40155-S11-1323-12-10/20



Table 5-4 Bill of materials (continued)				
Ref	Value	Specification		
F1	SFE10.7MA5-A or SKM107M1-A20-10	Murata Toko		
X2, X3	142-0701-801	Johnson		
X1, X4, S1, S5		2-pole pin connector		
S4		3-pole pin connector, or not equipped		
IC1	TDA 5200	Infineon		

Please note that in case of operation at 434 MHz a capacitor has to be soldered in place of L2 and an inductor in place of C6.

The following components are necessary in addition to the above mentioned ones for evaluation of the TDA5200 in conjunction with a Microchip HCS515 decoder.

Table 5-5 Bill of	of Materials Addendum	
Ref	Value	Specification
R21	22kΩ	0805, ± 5%
R22	100kΩ	0805, ± 5%
R23	22kΩ	0805, ± 5%
R24	820kΩ	0805, ± 5%
R25	560kΩ	0805, ± 5%
C21	100nF	1206, X7R, ± 10%
C22	100nF	1206, X7R, ± 10%
IC2	HCS515	Microchip
T1	BC 847B	Infineon
D1	LS T670-JL	Infineon



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